

PMV75UP,215 Datasheet



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DiGi Electronics Part Number PMV75UP,215-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PMV75UP,215

Description MOSFET P-CH 20V 2.5A TO236AB

Detailed Description P-Channel 20 V 2.5A (Ta) 490mW (Ta), 5W (Tc) Surf

ace Mount TO-236AB



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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PMV75UP,215	Nexperia USA Inc.
Series:	Product Status:
-	Active
FET Type:	Technology:
P-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
20 V	2.5A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:
1.8V, 4.5V	102m0hm @ 2.5A, 4.5V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
900mV @ 250μA	7.5 nC @ 4.5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±12V	550 pF @ 10 V
FET Feature:	Power Dissipation (Max):
	490mW (Ta), 5W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
TO-236AB	TO-236-3, SC-59, SOT-23-3
Base Product Number:	
PMV75	

Environmental & Export classification

8541.29.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



PMV75UP 20 V, P-channel Trench MOSFET 25 April 2014

Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Very fast switching
- Enhanced power dissipation capability: P_{tot} = 1000 mW

3. Applications

- LED driver
- Power management
- High-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	-20	V
V_{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-	-3.2	Α
Static characte	Static characteristics					,	
R _{DSon}	drain-source on-state resistance	V_{GS} = -4.5 V; I_D = -2.5 A; T_j = 25 °C		-	77	102	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



20 V, P-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u></u> 3	D
2	S	source		
3	D	drain	1 2	G Tr
			TO-236AB (SOT23)	S 017aaa257

6. Ordering information

Table 3. Ordering information

Type number	Package	ackage				
	Name	Description	Version			
PMV75UP	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV75UP	%CN

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C		-	-20	V
V_{GS}	gate-source voltage			-12	12	V
I _D	drain current	V _{GS} = -4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-3.2	Α
		V _{GS} = -4.5 V; T _{amb} = 25 °C	[1]	-	-2.5	Α
		V _{GS} = -4.5 V; T _{amb} = 100 °C	[1]	-	-1.6	Α
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-10	Α
P _{tot} total power di	total power dissipation	T _{amb} = 25 °C	[2]	-	490	mW
			[1]	-	1000	mW
		T _{sp} = 25 °C		-	5000	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drai	in diode	1	- I			
I _S	source current	T _{amb} = 25 °C	[1]	-	-0.9	Α

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

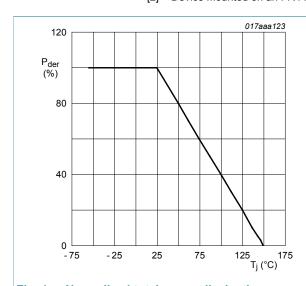


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

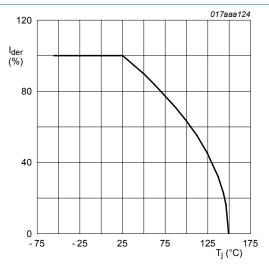


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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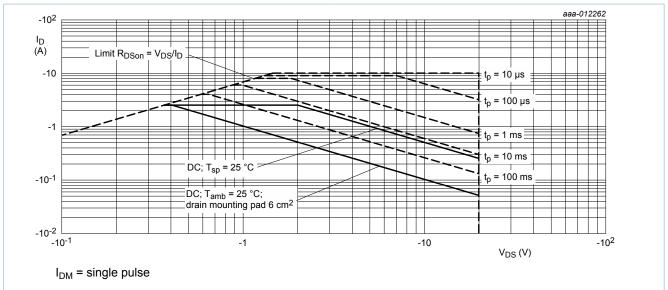


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

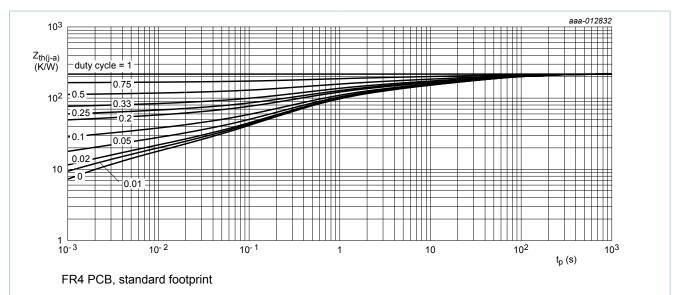
9. Thermal characteristics

Table 6. Thermal characteristics

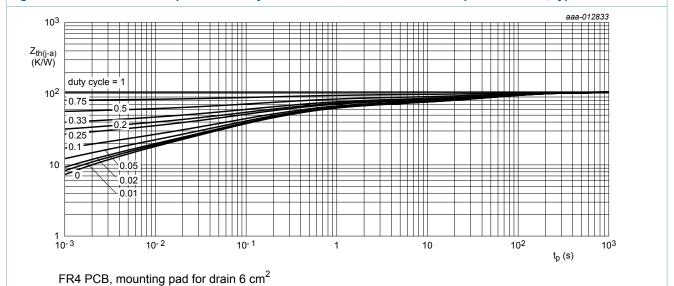
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
fro	thermal resistance	in free air	[1]	-	217	255	K/W
	from junction to ambient		[2]	-	105	124	K/W
	ambient	in free air; t ≤ 5 s	[2]	-	73	86	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	20	25	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

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Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values Fig. 5.

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics		-			
V _{(BR)DSS}	drain-source breakdown voltage	I_D = -250 μ A; V_{GS} = 0 V; T_j = 25 °C	-20	-	-	V
V_{GSth}	gate-source threshold voltage	I_D = -250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C	-0.47	-0.68	-0.9	V
I _{DSS}	drain leakage current	V _{DS} = -20 V; V _{GS} = 0 V; T _j = 25 °C	-	-	-1	μA
I _{GSS}	gate leakage current	V _{GS} = 12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		V _{GS} = -12 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-100	nA
R _{DSon} drain-source on-state	drain-source on-state	V_{GS} = -4.5 V; I_D = -2.5 A; T_j = 25 °C	-	77	102	mΩ
	resistance	V _{GS} = -4.5 V; I _D = -2.4 A; T _j = 150 °C	-	110	146	mΩ
		V_{GS} = -2.5 V; I_D = -2.2 A; T_j = 25 °C	-	95	125	mΩ
		V _{GS} = -1.8 V; I _D = -1 A; T _j = 25 °C	-	120	156	mΩ
9 _{fs}	forward transconductance	V_{DS} = -10 V; I_D = -2 A; T_j = 25 °C	-	15	-	S
R_G	internal gate resistance (AC)	f = 1 MHz	-	41	-	Ω
Dynamic ch	naracteristics		,			_
Q _{G(tot)}	total gate charge	V_{DS} = -10 V; I_{D} = -2.5 A; V_{GS} = -4.5 V;	-	5	7.5	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	0.7	-	nC
Q_{GD}	gate-drain charge		-	0.9	-	nC
C _{iss}	input capacitance	V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V;	-	550	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	63	-	pF
C _{rss}	reverse transfer capacitance		-	53	-	pF
t _{d(on)}	turn-on delay time	V_{DS} = -10 V; I_{D} = -2.5 A; V_{GS} = -4.5 V;	-	6	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega$; $T_j = 25 °C$	-	14	-	ns
$t_{d(off)}$	turn-off delay time		-	120	-	ns
t _f	fall time		-	50	-	ns
Source-dra	in diode					,
V _{SD}	source-drain voltage	I _S = -0.9 A; V _{GS} = 0 V; T _i = 25 °C	-	-0.8	-1.2	V

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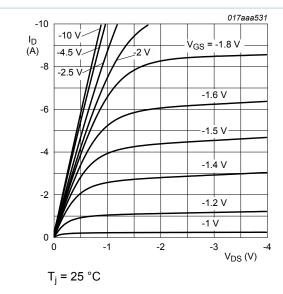


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

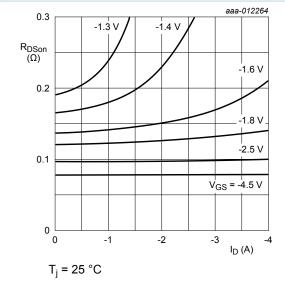


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

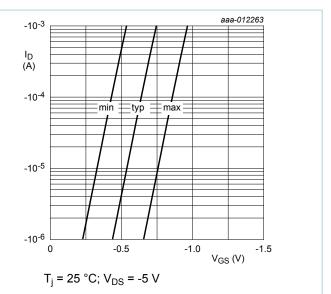


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

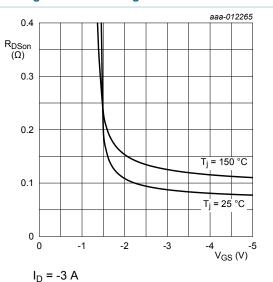


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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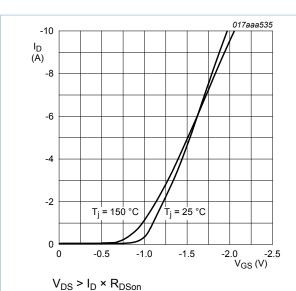


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

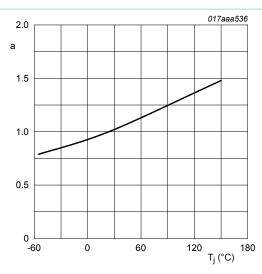


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

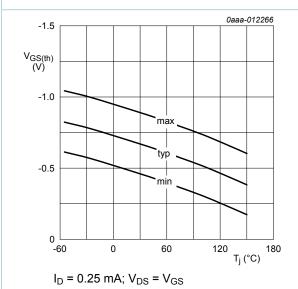
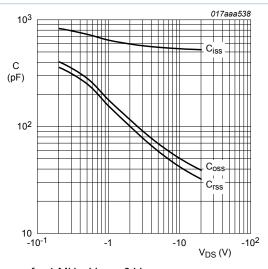


Fig. 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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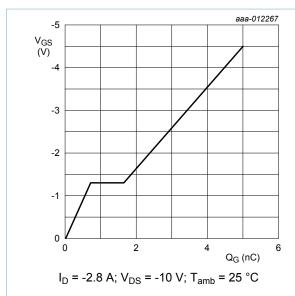


Fig. 14. Gate-source voltage as a function of gate charge; typical values

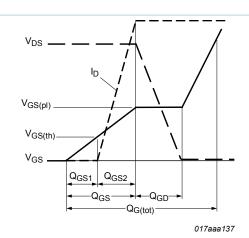


Fig. 15. Gate charge waveform definitions

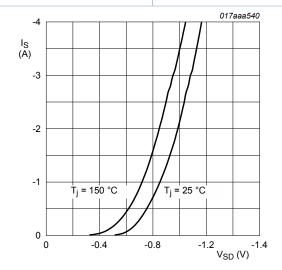


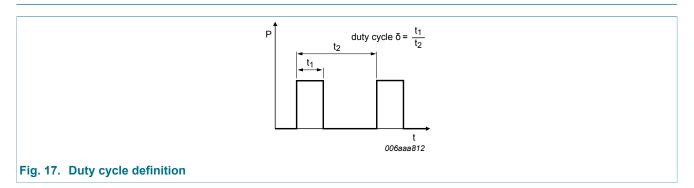
Fig. 16. Source current as a function of source-drain voltage; typical values

 $V_{GS} = 0 V$

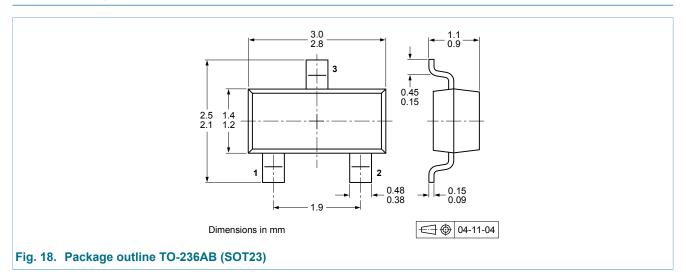
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11. Test information



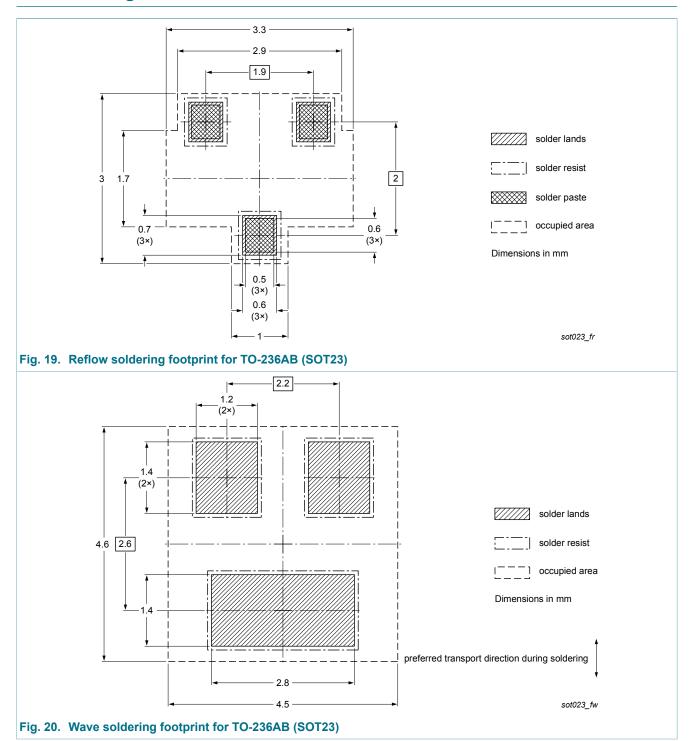
12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV75UP v.1	20140425	Product data sheet	-	-

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15. Legal information

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Document status [1][2]	Product status [3]	Definition
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